

ROHS COMPLIANT

Vishay Siliconix

Dual P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY								
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)					
- 20	0.295 at V _{GS} = - 4.5 V	- 2.6						
	0.420 at V _{GS} = - 2.5 V	- 2.2	1.6 nC					
	0.560 at V _{GS} = - 1.8 V	- 1.9						

FEATURES

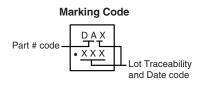
- Halogen-free
- TrenchFET[®] Power MOSFET
- New Thermally Enhanced PowerPAK[®] SC-75 Package
 - Small Footprint Area

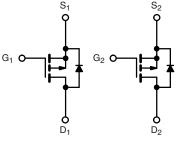
APPLICATIONS

Load Switch, PA Switch and Battery Switch for Portable
 Devices

D1 D2 1.60 mm 4 0rd

PowerPAK SC75-6L-Dual





Ordering Information: SiB911DK-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET P-Channel MOSFET

Parameter		Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	- 20	V		
Gate-Source Voltage		V _{GS}	± 8			
	T _C = 25 °C		- 2.6	A		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 70 °C	I _D	- 2.1			
Continuous Diain Current (15 = 150 °C)	T _A = 25 °C	U	- 1.5 ^{a, b}			
	T _A = 70 °C		- 1.2 ^{a, b}			
Pulsed Drain Current		I _{DM}	- 5			
Continuous Source-Drain Diode Current	T _C = 25 °C	I _S	- 2.6			
Continuous Source-Drain Diode Current	T _A = 25 °C	15	- 0.9 ^{a, b}			
	T _C = 25 °C		3.1	w		
Maximum Power Dissipation	T _C = 70 °C	P _D	2			
	T _A = 25 °C	' D	1.1 ^{a, b}	~ ~ ~		
	T _A = 70 °C		0.7 ^{a, b}			
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Temperature		260				

THERMAL RESISTANCE RATINGS									
Parameter	Symbol	Typical	Maximum	Unit					
Maximum Junction-to-Ambient ^{a, e}	t ≤ 5 s	R _{thJA}	90	115	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	32	40	0/11				

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. t = 5 s.

- c. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- d. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

e. Maximum under Steady State conditions is 125 °C/W.

f. Based on $T_C = 25 \ ^{\circ}C$.

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SPECIFICATIONS $T_J = 25 \text{ °C}$, unless otherwise noted									
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit			
Static	_			_					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = -250 \mu A$	- 20			V			
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = - 250 μA		- 19		mV/°C			
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	η - 200 μλ		1.9					
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 0.4		- 1	V			
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA			
Zero Gate Voltage Drain Current	Inco	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1				
Zero Gale voltage Diam Current	IDSS	V_{DS} = - 20 V, V_{GS} = 0 V, T_{J} = 55 °C	- 10	μA					
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 5 V$, $V_{GS} = -4.5 V$	5			Α			
		V _{GS} = - 4.5 V, I _D = - 1.5 A		0.242	0.295				
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 2.5 V, I _D = - 1.2 A		0.345	0.420	Ω			
		V _{GS} = - 1.8 V, I _D = - 0.18 A		0.455	0.560				
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 10 V, I _D = - 1.5 A		3		S			
Dynamic ^b						I			
Input Capacitance	C _{iss}			115		pF			
Output Capacitance	C _{oss}	V _{DS} = - 10 V, V _{GS} = 0 V, f = 1 MHz		30					
Reverse Transfer Capacitance	C _{rss}			20					
		V _{DS} = - 10 V, V _{GS} = - 8 V, I _D = - 1.7 A		2.6	4.0	- nC			
Total Gate Charge	Qg			1.6	2.5				
Gate-Source Charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 1.7 A		0.3					
Gate-Drain Charge	Q _{gd}			0.5					
Gate Resistance	R _g	f = 1 MHz		7		Ω			
Turn-On Delay Time	t _{d(on)}			12	20				
Rise Time	tr	V_{DD} = - 10 V, R _L = 7.1 Ω		45	70				
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ - 1.4 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		10	15				
Fall Time	t _f			31	50				
Turn-On Delay Time	t _{d(on)}			3	10	ns			
Rise Time	t _r	V_{DD} = - 10 V, R _L = 7.1 Ω		25	40	1			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong -1.4 \text{ A}, \text{ V}_{\text{GEN}} = -8 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		10	15				
Fall Time	t _f			10	15	1			
Drain-Source Body Diode Characteris	tics			1		<u> </u>			
Continuous Source-Drain Diode Current	۱ _S	T _C = 25 °C			- 2.6				
Pulse Diode Forward Current	I _{SM}				5	A			
Body Diode Voltage	V _{SD}	I _S = - 1.4 A, V _{GS} = 0 V		- 0.8	- 1.2	V			
Body Diode Reverse Recovery Time	t _{rr}			25	50	ns			
Body Diode Reverse Recovery Charge	Q _{rr}			26	50	nC			
Reverse Recovery Fall Time	ta	$I_F = -1.4 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^\circ\text{C}$		19					
Reverse Recovery Rise Time	t _b			6		ns			

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

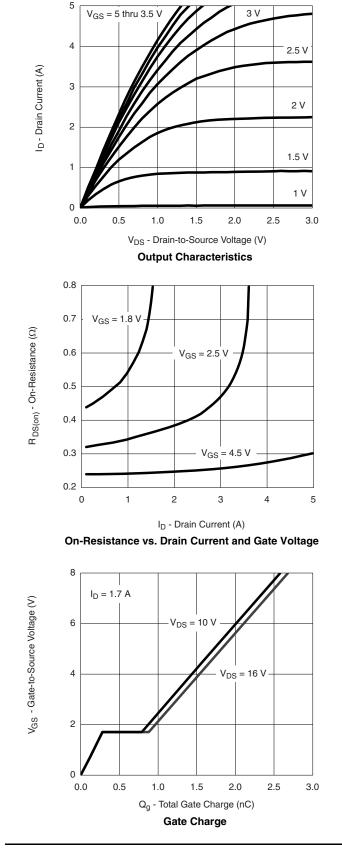
b. Guaranteed by design, not subject to production testing.

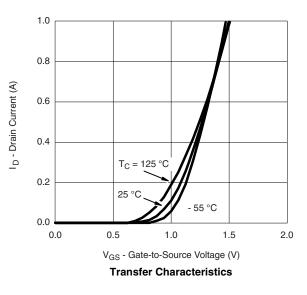
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

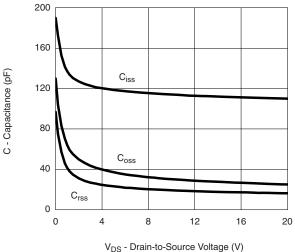


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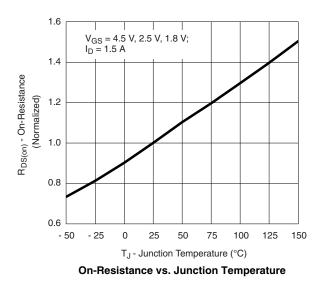








Capacitance

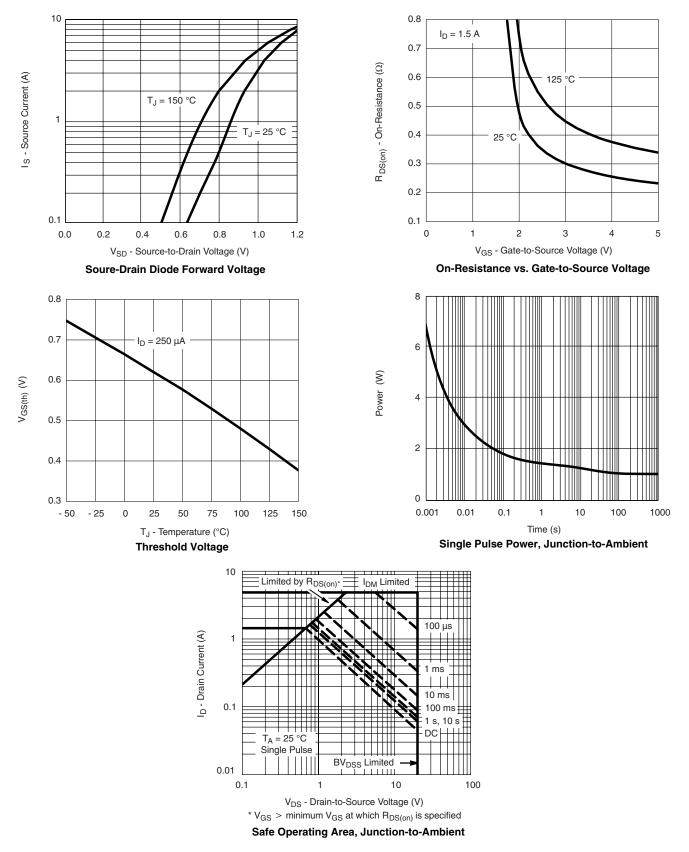


Document Number: 74475 S-80515-Rev. B, 10-Mar-08



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

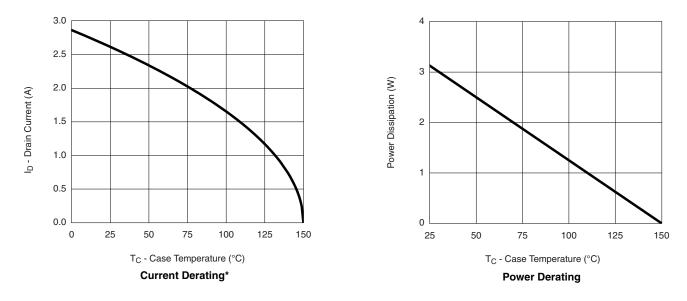






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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

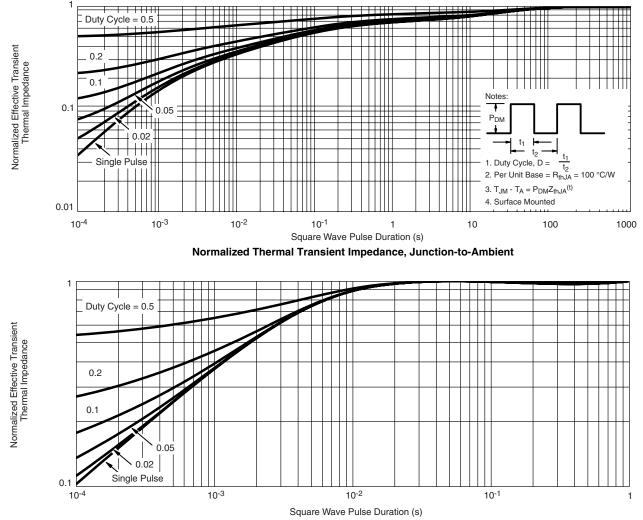


* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



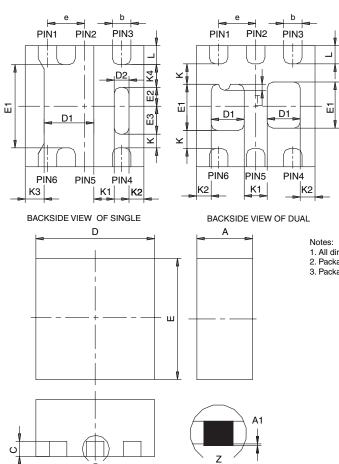
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?74475.

Package Information

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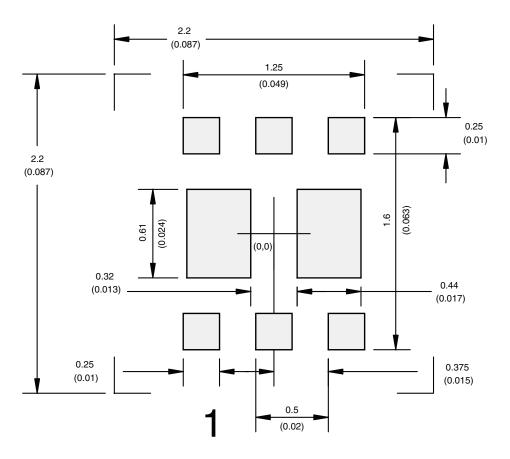
- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

DETAIL Z

		SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES			
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012							
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012							
E3	0.32	0.37	0.42	0.013	0.015	0.017							
е		0.50 BSC			0.020 BSC		0.50 BSC			0.020 BSC			
К		0.180 TYP			0.007 TYP		0.245 TYP			0.010 TYP			
K1		0.275 TYP			0.011 TYP		0.320 TYP			0.013 TYP			
K2	0.200 TYP 0.008 TYP				0.200 BSC			0.008 TYP					
K3	0.255 TYP 0.			0.010 TYP									
K4	0.300 TYP			0.012 TYP									
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
Т							0.03	0.08	0.13	0.001	0.003	0.005	
ECN: C-07431 – Rev. C, 06-Aug-07 DWG: 5935													



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Dual



Dimensions in mm/(Inches)

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